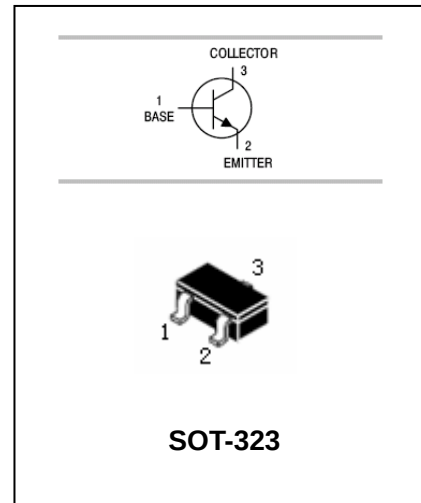


NPN General Purpose Transistor

MMST5551

FEATURES

- Epitaxial planar die construction.
- Complementary PNP type available (MMST5401).
- Also available in lead free version.



APPLICATIONS

- Ideal for medium power amplification and switching.

ORDERING INFORMATION

Type No.	Marking	Package Code
MMST5551	K4N	SOT-323

MAXIMUM RATING @ Ta=25°C unless otherwise specified

Symbol	Parameter	Value	UNIT
V_{CBO}	collector-base voltage	180	V
V_{CEO}	collector-emitter voltage	160	V
V_{EBO}	emitter-base voltage	6	V
I_C	collector current (DC)	0.6	A
P_C	Collector dissipation	0.3	W
T_j, T_{stg}	junction and storage temperature	-55-150	°C

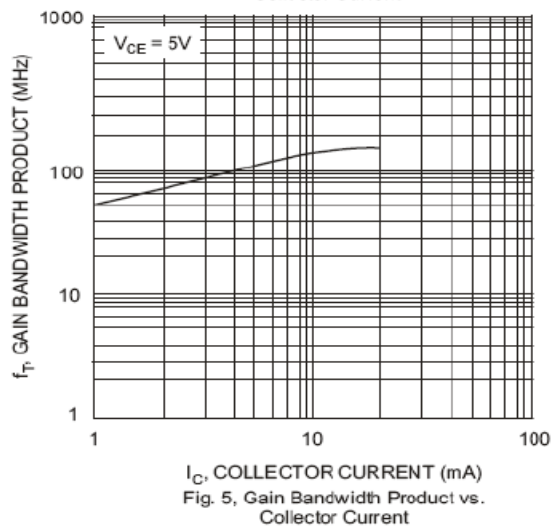
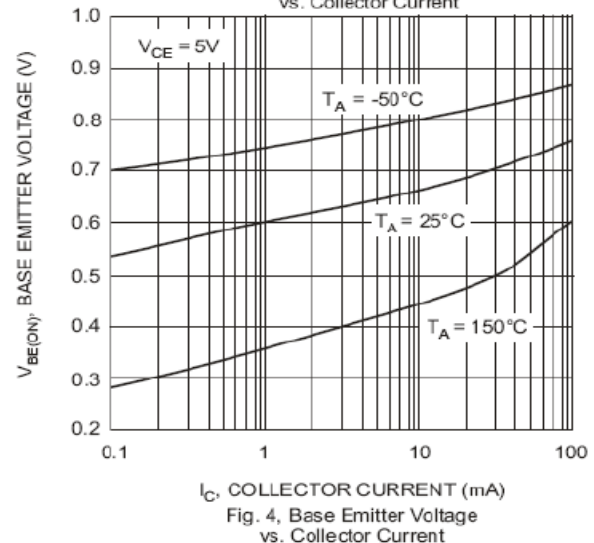
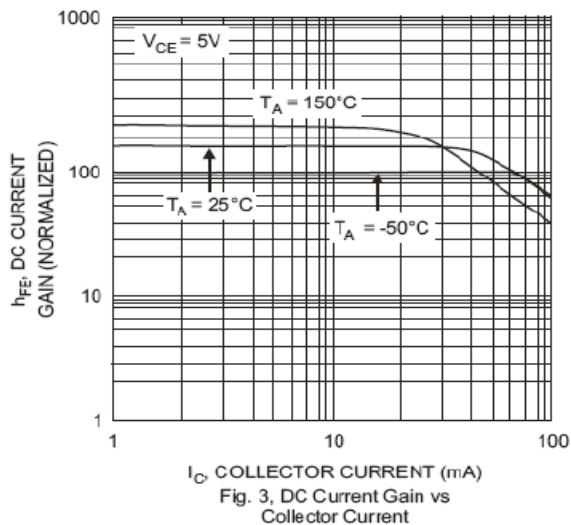
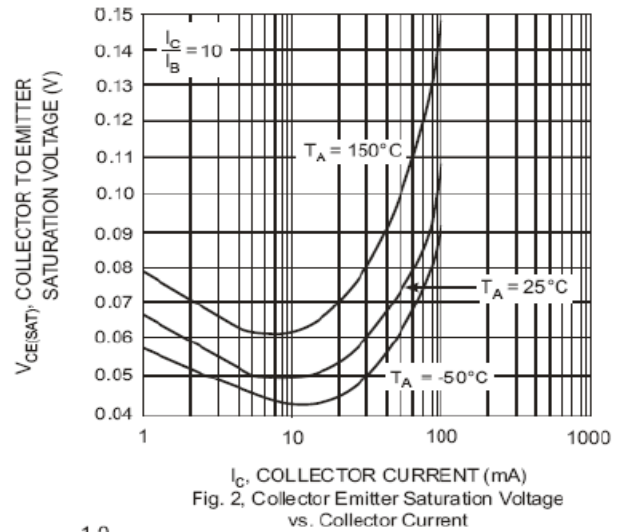
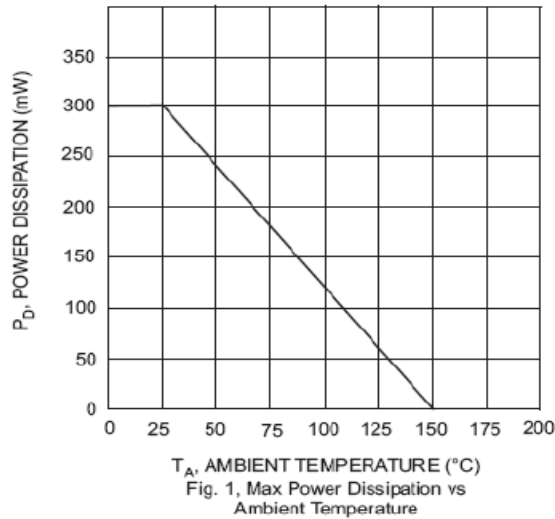
ELECTRICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified

Symbol	Parameter	Test conditions	MIN.	MAX.	UNIT
$V_{(BR)CBO}$	Collector-base breakdown voltage	$I_C=100\mu A, I_E=0$	180		
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C=0.1mA, I_B=0$	160		
$V_{(BR)EBO}$	Emitter-base breakdown voltage	$I_E=100\mu A, I_C=0$	6		
I_{CBO}	collector cut-off current	$I_E = 0; V_{CB} = 180V$	-	0.1	μA
I_{EBO}	emitter cut-off current	$I_C = 0; V_{EB} = 4V$	-	0.1	μA
h_{FE}	DC current gain	$V_{CE} = 5V; I_C = 1mA$ $V_{CE} = 5V; I_C = 10mA$ $V_{CE} = 5V; I_C = 50mA$	80 80 30	- 250 -	
$V_{CE(sat)}$	collector-emitter saturation voltage	$I_C = 50mA; I_B = 5mA$	-	0.5	V
$V_{BE(sat)}$	base-emitter saturation voltage	$I_C = 50mA; I_B = 5mA$	-	1	V
f_T	transition frequency	$I_C = 10mA; V_{CE} = 10V;$ $f = 100MHz$	80	-	MHz

NPN General Purpose Transistor

MMST5551

TYPICAL CHARACTERISTICS @ $T_a=25^\circ\text{C}$ unless otherwise specified



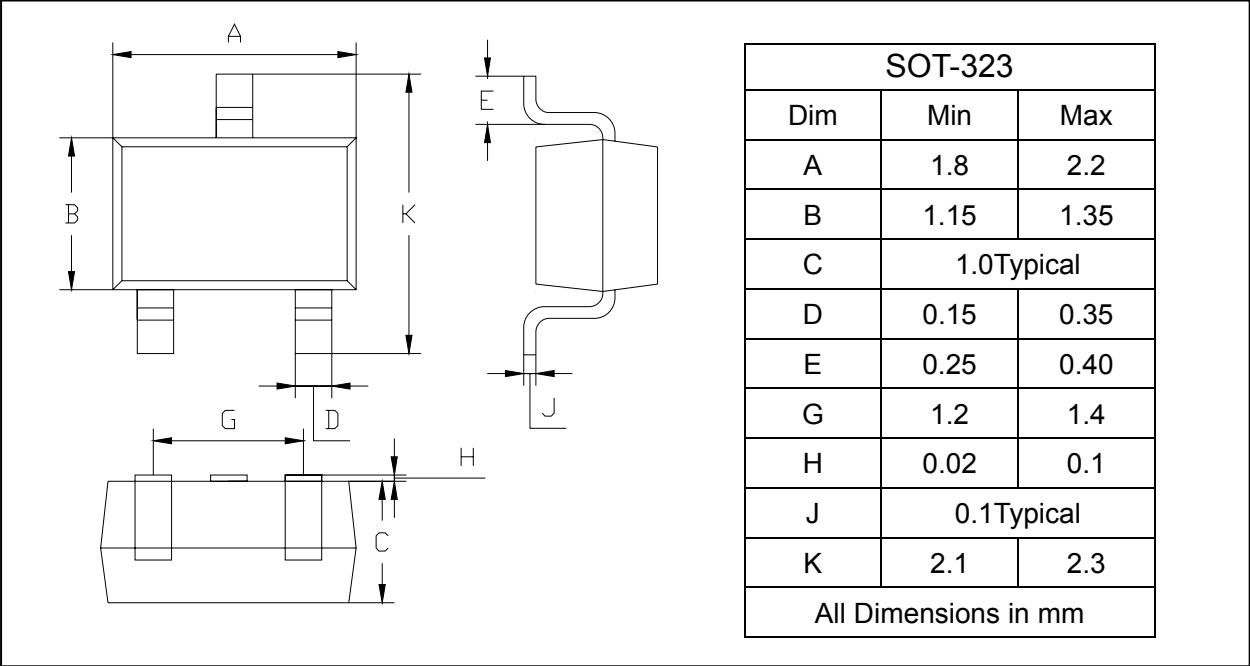
NPN General Purpose Transistor

MMST5551

PACKAGE OUTLINE

Plastic surface mounted package

SOT-323



PACKAGE INFORMATION

Device	Package	Shipping
MMST5551	SOT-323	3000/Tape&Reel